**Preferred Device** 

# Small Signal MOSFET 500 mA, 60 V

**N-Channel TO-92 (TO-226)** 

#### **Features**

• Pb-Free Package is Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	Vdc
Gate-Source Voltage - Continuous - Non-repetitive (t <sub>p</sub> ≤ 50 μs)	V <sub>GS</sub> V <sub>GSM</sub>	±20 ±40	Vdc Vpk
Drain Current (Note)	I <sub>D</sub>	0.5	Adc
Total Device Dissipation @ T <sub>A</sub> = 25°C	P <sub>D</sub>	350	mW
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

 The Power Dissipation of the package may result in a lower continuous drain current.

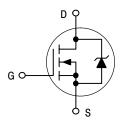


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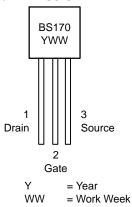
500 mA, 60 V  $R_{DS(on)} = 5 Ω$ 

# N-Channel





# MARKING DIAGRAM & PIN ASSIGNMENT



### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**Preferred** devices are recommended choices for future use and best overall value.

# **BS170**

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	
Gate Reverse Current (V <sub>GS</sub> = 15 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	-	0.01	10	nAdc
Drain-Source Breakdown Voltage (V <sub>GS</sub> = 0, I <sub>D</sub> = 100 μAdc)	V <sub>(BR)DSS</sub>	60	90	-	Vdc
ON CHARACTERISTICS (Note 1)					
Gate Threshold Voltage (V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.0 mAdc)	V <sub>GS(Th)</sub>	0.8	2.0	3.0	Vdc
Static Drain–Source On Resistance (V <sub>GS</sub> = 10 Vdc, I <sub>D</sub> = 200 mAdc)	r <sub>DS(on)</sub>	-	1.8	5.0	Ω
Drain Cutoff Current (V <sub>DS</sub> = 25 Vdc, V <sub>GS</sub> = 0 Vdc)	I <sub>D(off)</sub>	-	-	0.5	μΑ
Forward Transconductance (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 250 mAdc)	9fs	-	200	_	mmhos
SMALL-SIGNAL CHARACTERISTICS		•	•		•
Input Capacitance (V <sub>DS</sub> = 10 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	-	-	60	pF
SWITCHING CHARACTERISTICS					
Turn-On Time (I <sub>D</sub> = 0.2 Adc) See Figure 1	t <sub>on</sub>	-	4.0	10	ns
Turn-Off Time (I <sub>D</sub> = 0.2 Adc) See Figure 1	t <sub>off</sub>	-	4.0	10	ns

<sup>1.</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BS170	TO-92 (TO-226)	1000 Unit / Box
BS170G	TO-92 (TO-226) (Pb-Free)	1000 Unit / Box
BS170RLRA		2000 Tape & Reel
BS170RLRM		2000 Tape & Ammo Box
BS170RLRP	TO-92 (TO-226)	2000 Tape & Ammo Box
BS170RL1		2000 Tape & Reel
BS170ZL1		2000 Tape & Ammo Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **RESISTIVE SWITCHING**

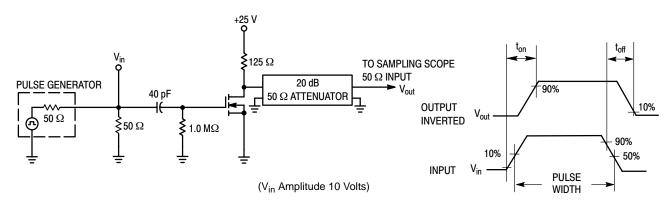


Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

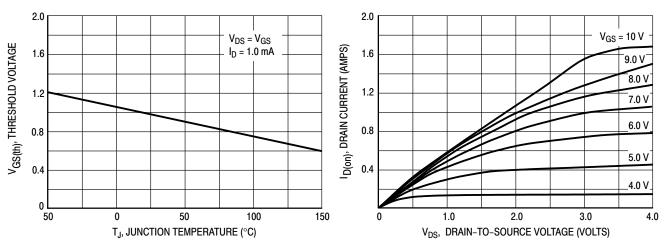


Figure 3. V<sub>GS(th)</sub> Normalized versus Temperature

Figure 4. On-Region Characteristics

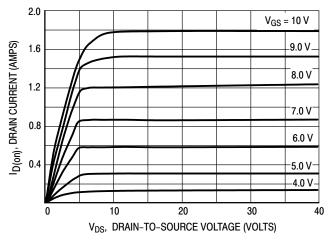


Figure 5. Output Characteristics

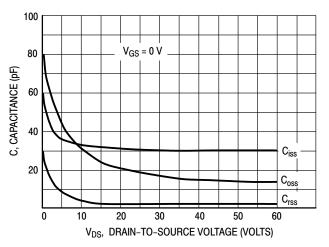
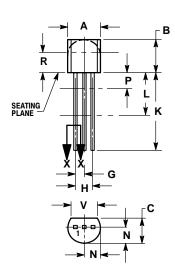


Figure 6. Capacitance versus Drain-To-Source Voltage

#### **BS170**

#### PACKAGE DIMENSIONS

# TO-92 (TO-226) CASE 29-11 ISSUE AL





#### NOTES:

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   M
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
   IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

#### STYLE 30:

- PIN 1. DRAIN
  - 2. GATE
  - 3. SOURCE

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